

Vishay Siliconix

Improved Quad CMOS Analog Switches

DESCRIPTION

The DG211B, DG212B analog switches are highly improved versions of the industry-standard DG211, DG212. These devices are fabricated in Vishay Siliconix' proprietary silicon gate CMOS process, resulting in lower on-resistance, lower leakage, higher speed, and lower power consumption.

These quad single-pole single-throw switches are designed for a wide variety of applications in telecommunications, instrumentation, process control, computer peripherals, etc. An improved charge injection compensation design minimizes switching transients. The DG211B and DG212B can handle up to \pm 22 V, and have an improved continuous current rating of 30 mA. An epitaxial layer prevents latchup.

All devices feature true bi-directional performance in the on condition, and will block signals to the supply levels in the off condition.

The DG211B is a normally closed switch and the DG212B is a normally open switch (see Truth Table).

BENEFITS

- Wide analog signal range
- Simple logic interface
- Higher accuracy
- Minimum transients
- Reduced power consumption
- Superior to DG211, DG212
- Space savings (TSSOP)

FEATURES

- ± 22 V supply voltage rating
- TTL and CMOS compatible logic
- Low on-resistance R_{DS(on)}: 50 Ω
- Low leakage I_{D(on)}: 20 pA
- Single supply operation possible
- Extended temperature range
- Fast switching ton: 120 ns
- Low charge injection Q: 1 pC
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

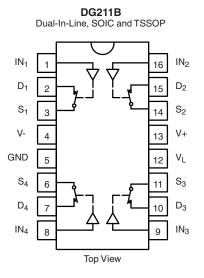
Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Industrial instrumentation
- Test equipment
- · Communications systems
- Disk drives
- Computer peripherals
- Portable instruments
- Sample-and-hold circuits

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



TRUTH TABLE						
LOGIC	DG211B	DG212B				
0	On	Off				
1	Off	On				

Note

 Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V





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ORDERING INFORMATION					
TEMP. RANGE	PACKAGE	PART NUMBER			
-40 °C to +85 °C		DG211BDY-E3 DG211BDY-T1-E3			
	16-pin narrow SOIC	DG212BDY-E3 DG212BDY-T1-E3			
		DG211BDQ-E3 DG211BDQ-T1-E3			
	16-pin TSSOP	DG212BDQ-E3 DG212BDQ-T1-E3			
	16-pin plastic DIP	DG211BDJ-E3			
		DG212BDJ-E3			

ABSOLUTE MAXIMUM R	ATINGS ($T_A = 25 ^{\circ}C$, unless other	wise noted)			
PARAMETER		LIMIT	UNIT		
Voltages referenced, V+ to V-		44			
GND		25			
Digital inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first			
Current (any terminal)		30	0		
Peak current, S or D (pulsed at 1 m	ns, 10 % duty cycle max.)	100	- mA		
Storage temperature		-65 to +125	°C		
Power dissipation (package) ^b	16-pin plastic DIP ^c	470			
	16-pin narrow SOIC and TSSOP ^d	640	mW		

Notes

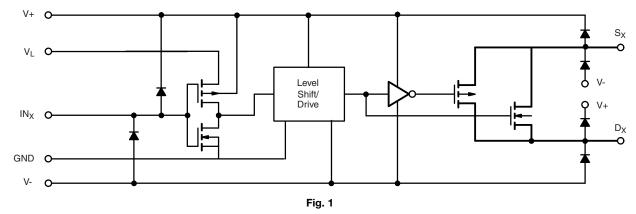
a. Signals on SX, DX, or INX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings

b. All leads welded or soldered to PC board

c. Derate 6.5 mW/°C above 75 °C

d. Derate 7.6 mW/°C above 75 °C

SCHEMATIC DIAGRAM (typical channel)





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SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. ^a	D SUFFIX -40 °C to +85 °C			UNIT
	OTMOOL	V+ = 15 V, V- = -15 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V ^e		MIN. ^b	۲YP. ۵	MAX. ^b	UNIT
Analog Switch			-				
Analog signal range ^d	V _{ANALOG}		Full	-15	-	15	V
Drain-source on-resistance	Passa		Room	-	45	85	Ω
	R _{DS(on)}	$V_{D} = \pm 10 \text{ V}, \text{ I}_{S} = 1 \text{ mA}$	Full	-	-	100	
R _{DS(on)} match	$\Delta R_{DS(on)}$		Room	-	2	-	
Source off leakage current	la con	$V_{S} = \pm 14 \text{ V}, V_{D} = \pm 14 \text{ V}$	Room	-0.5	± 0.01	0.5	
Source on leakage current	I _{S(off)}	$v_{\rm S} = \pm 14 v$, $v_{\rm D} = \pm 14 v$	Full	-	± 0.01	5	
Drain off leakage current	le con	$V_{D} = \pm 14 \text{ V}, \text{ V}_{S} = \pm 14 \text{ V}$	Room	-0.5	± 0.01	0.5	nA
Drain on leakage current	I _{D(off)}	$v_{\rm D} = \pm 14 v, v_{\rm S} = \pm 14 v$	Full	-5	± 0.01	5	
Drain on leakage current		$V_{S} = V_{D} = \pm 14 V$	Room	-0.5	± 0.02	0.5	
Drain on leakage current	I _{D(on)}	vg = vD = ± 14 v	Full	-10	± 0.02	10	
Digital Control							
Input voltage high	V _{INH}		Full	2.4	-	-	V
Input voltage low	V _{INL}		Full	-	-	0.8	v
Input current	$I_{\rm INH}$ or $I_{\rm INL}$	V _{INH} or V _{INL}	Full	-1	-	1	μA
Input capacitance	C _{IN}		Room	-	5	-	pF
Dynamic Characteristics							
Turn-on time	t _{on}	V _S = 10 V, see Fig. 9	Room	-	-	300	ns
Turn-off time	t _{off}	$v_{\rm S} = 10$ v, see Fig. 9	Room	-	-	200	115
Charge injection	Q	C_L = 1000 pF, V_{gen} = 0 V, R_{gen} = 0 Ω	Room	-	1	-	рС
Source-off capacitance	C _{S(off)}	V _S = 0 V, f = 1 MHz	Room	-	5	-	
Drain-off capacitance	C _{D(off)}	$v_{\rm S} = 0$ V, $I = 1$ MHZ	Room	-	5	-	pF
Channel-on capacitance	C _{D(on)}	$V_D = V_S = 0 V$, f = 1 MHz	Room	-	16	-	
Off isolation	O _{IRR}	$C_{L} = 15 \text{ pF}, R_{L} = 50 \Omega,$	Room	-	90	-	dB
Channel to channel crosstalk	X _{TALK}	$V_{S} = 1 V_{RMS}$, f = 100 kHz	Room	-	95	-	uБ
Power Supply							
Positivo supply surrent	urrent I+	V OVer 5 V	Room	-	-	10	μA
Positive supply current	1+		Full	-	-	50	
Negative supply current	-	$V_{IN} = 0 V \text{ or } 5 V$	Room	- 10	-	-	
	1-		Full	- 50	-	-	μΑ
			Room	-	-	10	
Logic supply current	۱L		Full	-	-	50	
Power supply range for continuous operation	V _{OP}		Full	± 4.5	-	± 22	V



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SPECIFICATIONS (for Sir	ngle Supply)					
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. ^a	D SUFFIX -40 °C to +85 °C			UNIT
	01111D0L	V+ = 12 V, V- = 0 V V _L = 5 V, V _{IN} = 2.4 V, 0.8 V $^{\rm e}$		MIN. ^b	۲YP. ۵	MAX. ^b	
Analog Switch							
Analog signal range ^d	V _{ANALOG}		Full	0	-	12	V
Drain-source on-resistance	р		Room	-	90	160	
Drain-source on-resistance	R _{DS(on)}	V _D = 3 V, 8 V, I _S = 1 mA	Full	-	90	200	Ω
Dynamic Characteristics							
Turn-on time	t _{ON}		Room	-	-	300	20
Turn-off time	t _{OFF}	V _S = 8 V, see Fig. 1	Room	-	-	200	ns
Charge injection	Q	C_L = 1 nF, V_{gen} = 6 V, R_{gen} = 0 Ω	Room	-	4		рС
Power Supply							
Positivo oupply ourront	I+		Room	-	-	10	- μΑ
Positive supply current		$V_{IN} = 0 V \text{ or } 5 V$	Full	-	-	50	
Negative eventy every	I-		Room	- 10	-	-	
Negative supply current			Full	- 50	-	-	
	ΙL		Room	-	-	10	
Logic supply current		$V_{S} = 8 V$, see Fig. 1	Full	-	-	50	
Power supply range for continuous operation	V _{OP}		Full	+ 4.5	-	+ 25	V

Notes

a. Room = 25 °C, Full = as determined by the operating temperature suffix

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet

c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing

d. Guaranteed by design, not subject to production test

e. V_{IN} = input voltage to perform proper function

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

110 $R_{DS(on)}$ - Drain-Source On-Resistance ($\Omega)$ 100 90 ± 5 V 80 70 ± 10[']V 60 50 ± 15 V 40 20 V 30 20 10 0 8 -20 -16 -12 -8 - 4 12 16 20 4 V_D - Drain Voltage (V)

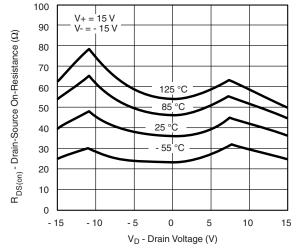
R_{DS(on)} vs. V_D and Power Supply Voltages

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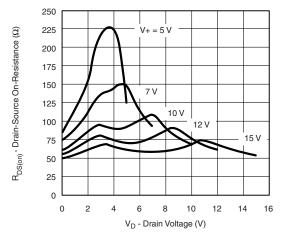


R_{DS(on)} vs. V_D and Temperature

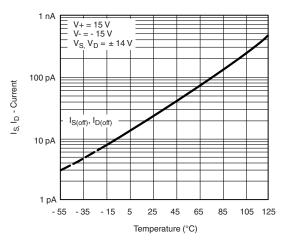


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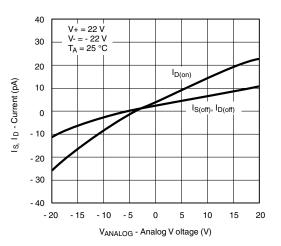
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



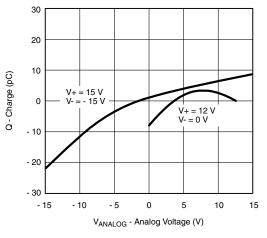
R_{DS(on)} vs. V_D and Single Power Supply Voltages



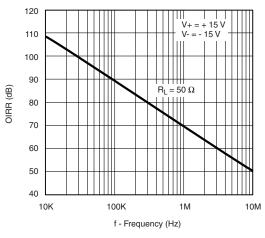
Leakage Current vs. Temperature



Leakage Current vs. Temperature



 $\mathbf{Q}_{S}, \mathbf{Q}_{D}$ - Charge Injection vs. Analog Voltage



Off Isolation vs. Frequency

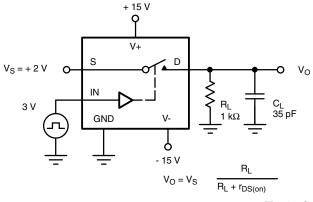
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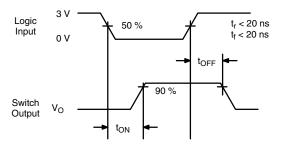
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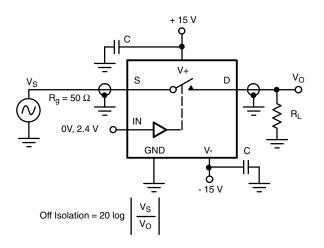
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TEST CIRCUITS











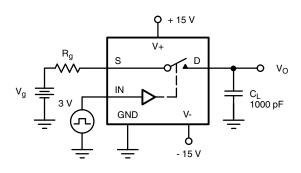


Fig. 5 - Charge Injection

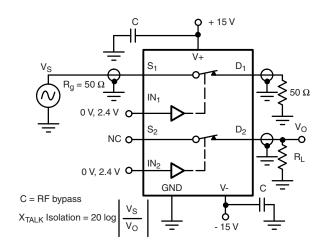
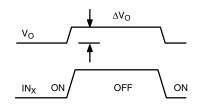


Fig. 4 - Channel to Channel Crosstalk



 ΔV_O = measured voltage error due to charge injection The charge injection in coulombs is Q = C_L x ΔV_O



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APPLICATIONS

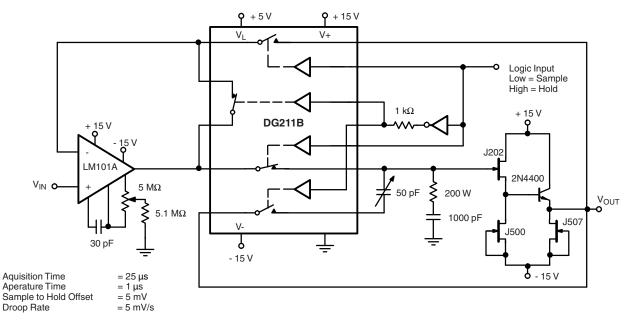
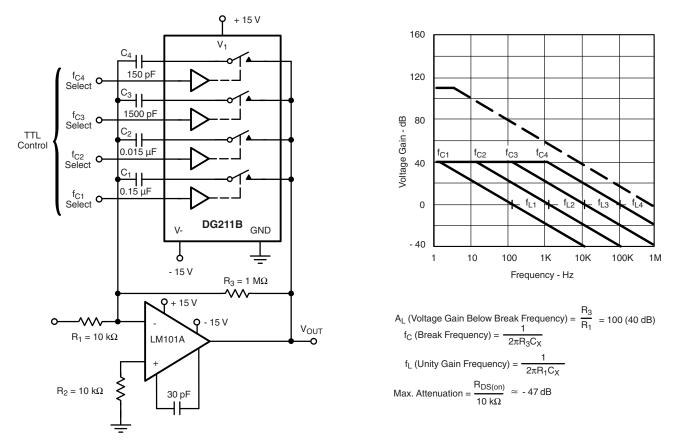


Fig. 6 - Sample and Hold







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APPLICATIONS

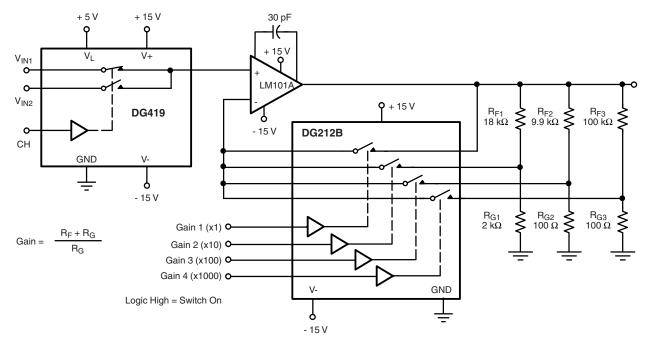


Fig. 8 - A Precision Amplifier with Digitally Programmable Input and Gains

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DG211B, DG212B

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PRODUCT SUMMARY							
Part number	DG211B	DG211B	DG211B	DG212B	DG212B	DG212B	
Status code	2	2	2	2	2	2	
Configuration	SPST x 4, NC	SPST x 4, NC	SPST x 4, NC	SPST x 4, NO	SPST x 4, NO	SPST x 4, NO	
Single supply min. (V)	5	5	5	5	5	5	
Single supply max. (V)	36	36	36	36	36	36	
Dual supply min. (V)	5	5	5	5	5	5	
Dual supply max. (V)	36	36	36	36	36	36	
On-resistance (Ω)	22	22	22	22	22	22	
Charge injection (pC)	45	45	45	45	45	45	
Source on capacitance (pF)	1	1	1	1	1	1	
Source off capacitance (pF)	-	-	-	-	-	-	
Leakage switch on typ. (nA)	5	5	5	5	5	5	
Leakage switch off max. (nA)	0.02	0.02	0.02	0.02	0.02	0.02	
-3 dB bandwidth (MHz)	0.5	0.5	0.5	0.5	0.5	0.5	
Package	TSSOP-16	SO-16 (narrow) AS	Plastic DIP-16	TSSOP-16	SO-16 (narrow) AS	Plastic DIP-16	
Functional circuit / applications	Multi purpose, instrumentation, medical and healthcare						
Interface	Parallel	Parallel	Parallel	Parallel	Parallel	Parallel	
Single supply operation	Yes	Yes	Yes	Yes	Yes	Yes	
Dual supply operation	Yes	Yes	Yes	Yes	Yes	Yes	
Turn on time max. (ns)	300	300	300	300	300	300	
Crosstalk and off isolation	-90	-90	-90	-90	-90	-90	

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?61556.

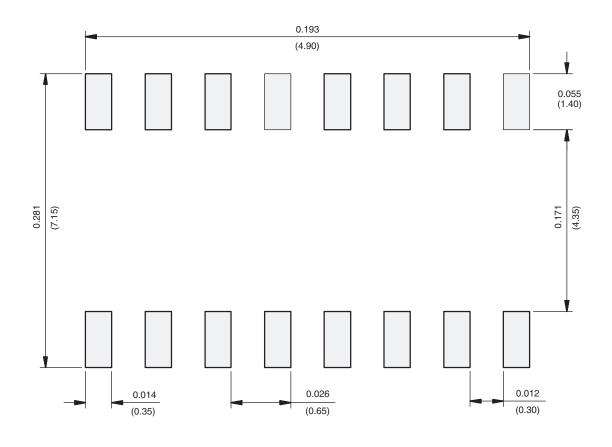
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PAD Pattern

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RECOMMENDED MINIMUM PAD FOR TSSOP-16



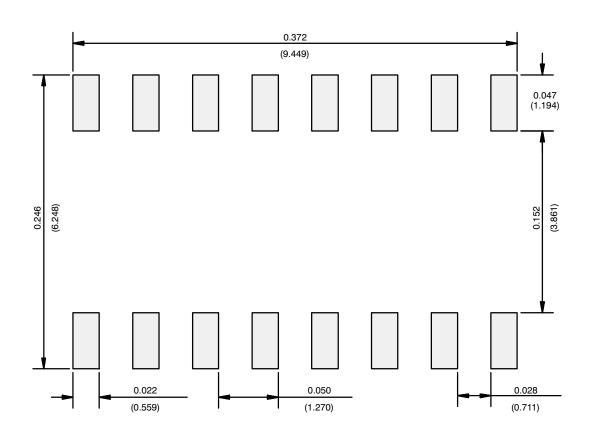
Recommended Minimum Pads Dimensions in inches (mm)

Application Note 826

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RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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